





70V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C	
70V	0.13Ω @ $V_{GS} = 10V$	3.8A	

Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control
- Class D Audio Output Stages

Features and Benefits

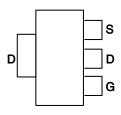
- Low On-Resistance
- · Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

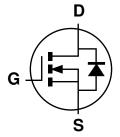
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)







Pin Out - Top View



Equivalent Circuit

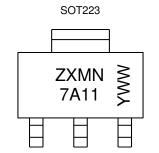
Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
ZXMN7A11GTA	Standard	SOT223	1,000 / Tape & Reel
ZXMN7A11GTC	Standard	SOT223	4,000 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMN 7A11 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	70	V
Gate-Source Voltage	V _G	±20	V	
Continuous Drain Current, V _{GS} = 10V,	$T_A = +25^{\circ}\text{C (Note 6)}$ $T_A = +70^{\circ}\text{C (Note 6)}$ $T_A = +25^{\circ}\text{C (Note 5)}$	Ι _D	3.8 3.0 2.7	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	5	Α	
Pulsed Drain Current	I _{DM}	10	Α	
Pulsed Source Current (Body Diode)	I _{SM}	10	Α	

Thermal Resistance ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation at TA = +25°C (Note 5)	В	2.0	W
Linear Derating Factor (Note 5)	P _D	16	mW/°C
Total Power Dissipation at TA = +25°C (Note 6) Linear Derating Factor (Note 6)	P _D	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	32	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

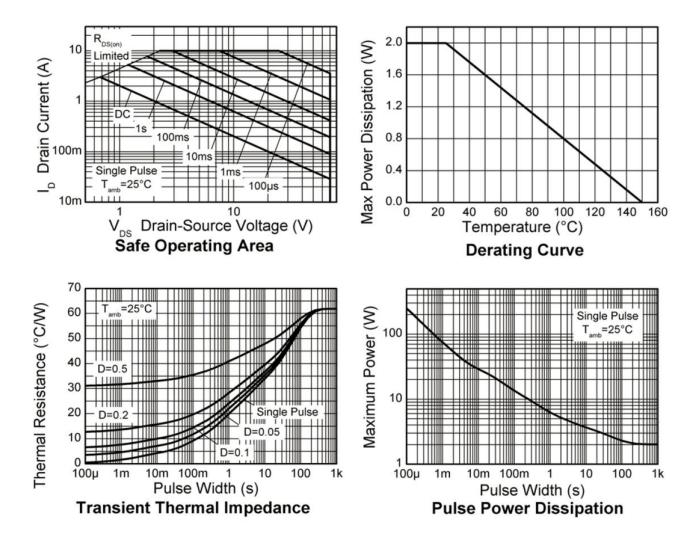
Notes:

^{5.} For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on FR4 PCB measured at t ≤ 5 sec.

 $^{7. \} Repetitive\ rating\ 25mm\ x\ 25mm\ FR4\ PCB,\ D=0.05\ pulse\ width=10\mu s\ -\ pulse\ width\ limited\ by\ maximum\ junction\ temperature.$



Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

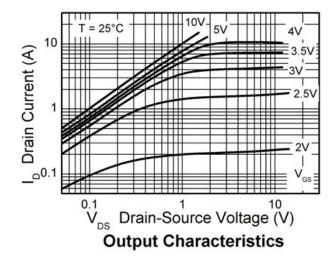
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	70	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 70V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS				•	•		
Gate Threshold Voltage	V _{GS(th)}	1.0	_	_	V	$V_{DS} = V_{GS}, I_D = 250\mu A$	
Static Dunin Course On Desigtance (Note 9)	Б	_	_	0.13	Ω	$V_{GS} = 10V, I_D = 4.4A$	
Static Drain-Source On-Resistance (Note 8)	R _{DS} (ON)	_	_	0.19	Ω	V _{GS} = 4.5V, I _D = 3.8A	
Forward Transfer Admittance	9 _{fs}	_	4.66	_	S	V _{DS} = 15V, I _D = 4.4A	
Diode Forward Voltage (Note 8)	V_{SD}	_	0.85	0.95	V	$T_J = +25^{\circ}C$, $V_{GS} = 0V$, $I_S = 2.5A$	
DYNAMIC CHARACTERISTICS (Notes 9 &10)							
Input Capacitance	C _{iss}	_	298	_		V _{DS} = 50V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	35	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	21	_			
Total Gate Charge	Qg	_	4.35	_	nC	$V_{DS} = 35V, V_{GS} = 5.0V, I_D = 4.4A$	
Total Gate Charge	Qg	_	7.4	_			
Gate-Source Charge	Q_{gs}	_	1.06	_	nC	$V_{DS} = 35V, V_{GS} = 10V, I_D = 4.4A$	
Gate-Drain Charge	Q_{gd}	_	1.8	_			
Turn-On Delay Time	t _{D(on)}	_	1.9	_	V _{DS} = 35V, V _{GS} = 10V,		
Turn-On Rise Time	t _r	_	2	_			
Turn-Off Delay Time	t _{D(off)}	_	11.5	_	ns	$I_D = 1 \text{ A}, R_G \cong 6.0\Omega$	
Turn-Off Fall Time	t _f	_	5.8	_			
Body Diode Reverse Recovery Time	t _{rr}	_	19.8	_	ns	$T_J = +25^{\circ}C$, $IS = 2.5A$,	
Body Diode Reverse Recovery Charge	Qrr		14		nC	dI/dt = 100A/μs	

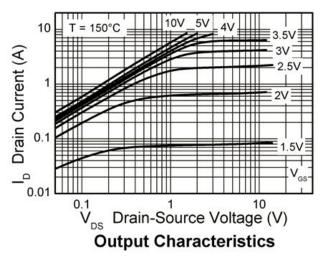
Notes:

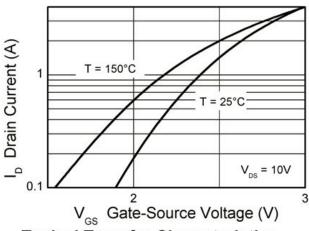
^{8.} Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

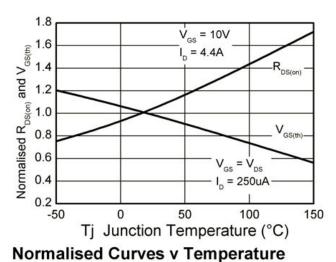


Typical Characteristics

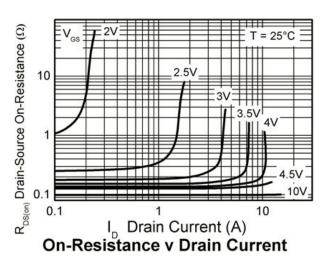


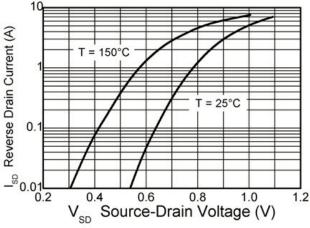






Typical Transfer Characteristics

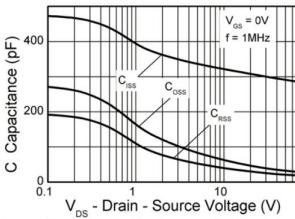




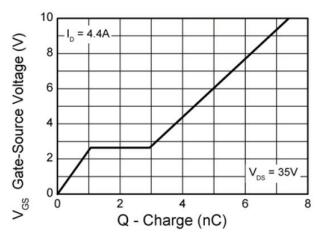
Source-Drain Diode Forward Voltage



Typical Characteristics



Capacitance v Drain-Source Voltage

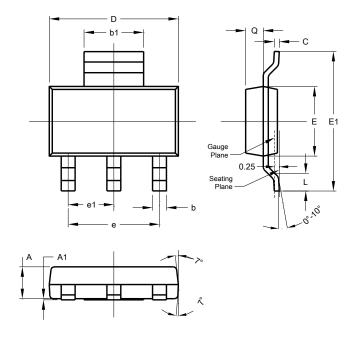


Gate-Source Voltage v Gate Charge



Package Outline Dimensions

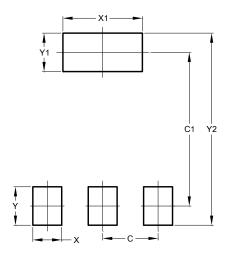
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A 1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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